Finding Negative Vacancy Formation Energies in Amorphous Silicon

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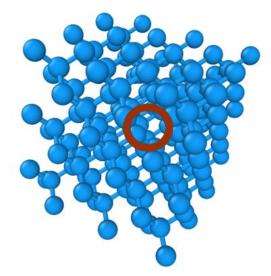
Collaborators:

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Dr Peng Chen

Introduction

- Goal: determine whether Amorphous Silicon has negative vacancy formation energies.
- Vacancies control diffusion in solids
- Vacancy formation energies
- Amorphous solids



Methodology



- Using LAMMPS software to conduct atomic simulations of amorphous silicon structures
- ADA Cluster at Texas A&M HPRC
- 20 cores with 2560 MB for between 20 and 100 Hrs.

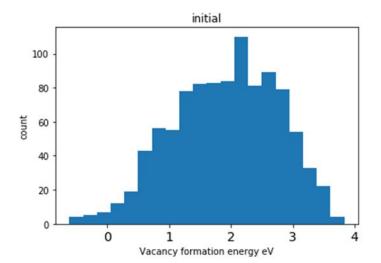


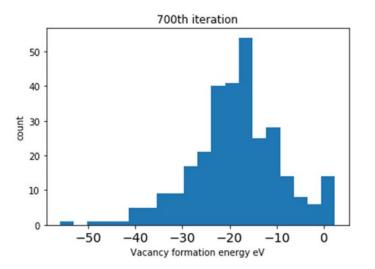
Project Overview

- 1. Melt and quench simulations
- 2. Preliminary vacancy formation energy calculation
- 3. Generalized atom removal energy calculations
- 4. Repeated calculations for varied simulation size
- 5. Self Interstitial formation energy calculations

Vacancy Formation Energy Histograms

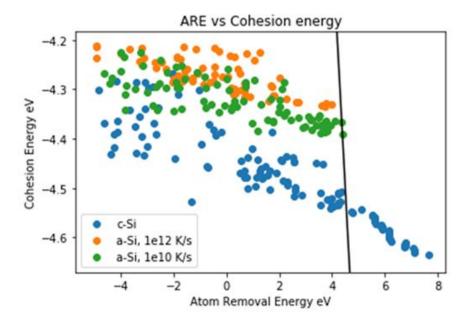
Performing algorithm on a-Si structures of 1000 atoms cooled at rates of 10^10 and 10^12K/s.





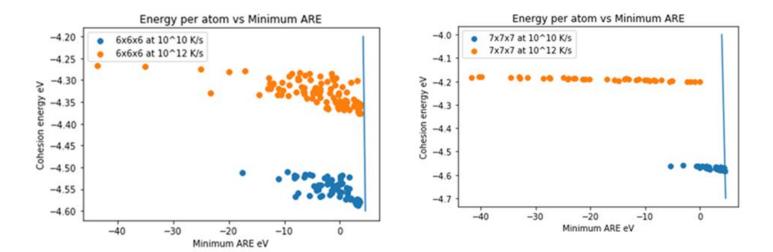


 Atom removal Energy vs Atom Cohesion Energy

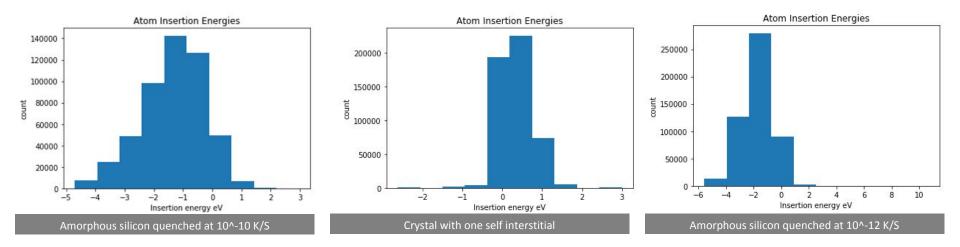




• ARE calculations for varied sizes



Self Interstitial formation Energies



Conclusion

- •
- Found that Amorphous Silicon has negative vacancy formation energies.
- Results suggest negative vacancy formation energy is due to relaxation in structures.
- A prior experimental study shows bulk amorphous silicon continuously relaxing into a crystalline form¹.
- More research is required to fully understand this phenomenon.

^{1.} S. Roorda, W. C. Sinke, J. M. Poate, D. C. Jacobson, S. Dierker, B. S. Dennis, D. J. Eaglesham, F. Spaepen, and P. Fuoss, Phys. Rev. B 44, 3702 (1991).

Acknowledgements

- Dr. Michael Demkowicz and Dr. Peng Chen
- Department of Energy, National Nuclear Security Administration. Award No. DE-NA0003857
- Center for Research Excellence of Dynamically Deformed Solids
- Online REU Program at Texas A&M
- HPRC at Texas A&M